

## AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method for the production of an antifalsification identification element including at least one layer reflecting electromagnetic waves, one spacer layer and one layer formed of metallic clusters, the method comprising:

applying a partial layer or an all-over layer which reflects electromagnetic waves onto a carrier substrate;

after said applying the layer which reflects electromagnetic waves, applying at least one partial polymeric layer and/or all-over polymeric layer of defined thickness onto the carrier substrate to form a spacer layer;

modifying the spacer layer by a process selected from a group consisting of a PVD process, a CVD process, and treatment with oxidizing fluids; and

applying a layer formed of metallic clusters onto the spacer layer, the layer formed of metallic clusters being produced by a method of vacuum technology or by solvent-based ~~systems; systems.~~

wherein said carrier substrate constitutes a first carrier substrate,

wherein said applying the layer formed of metallic clusters includes applying the layer formed of metallic clusters onto a second carrier substrate, and

wherein the first carrier substrate and the second carrier substrate are connected so as to form the antifalsification identification element after said applying the layer which reflects electromagnetic waves and said applying polymeric layer, and after said applying the layer formed of metallic clusters.

2. (Currently Amended) A method for the production of an antifalsification identification element including at least one layer reflecting electromagnetic waves, one spacer layer and one layer formed of metallic clusters, the method comprising:

applying a layer formed of metallic clusters onto a carrier substrate, the layer formed of metallic clusters being produced by a method of vacuum technology or by solvent-based systems;

after said applying the layer formed of metallic clusters, applying at least one partial polymeric layer and/or all-over polymeric layer of defined thickness onto the carrier substrate to form a spacer layer;

modifying the spacer layer by a process selected from a group consisting of a PVD process, a CVD process, and treatment with oxidizing fluids; and

applying a partial layer or an all-over layer reflecting electromagnetic waves onto the spacer ~~layer, layer,~~

wherein said carrier substrate constitutes a first carrier substrate,

wherein said applying the layer reflecting electromagnetic waves includes applying the layer reflecting electromagnetic waves onto a second carrier substrate and wherein said applying the polymeric layer includes applying the polymeric layer onto the second carrier substrate, and

wherein the first carrier substrate and the second carrier substrate are connected so as to form the antifalsification identification element after said applying the layer which reflects electromagnetic waves and said applying polymeric layer, and after said applying the layer formed of metallic clusters.

3. (Cancelled)

4. (Previously Presented)     The method of claim 1, wherein a protective layer is applied onto the layer formed of metallic clusters.

5. (Cancelled)

6. (Previously Presented)     The method of claim 1, wherein the spacer layer is structured through decrosslinking effects.

7. (Previously Presented)     The method of claim 6, characterized in that the decrosslinking structures of the spacer layer are converted into unique codes by means of fingerprint algorithms.

8. (Previously Presented)     The method of claim 1, wherein the spacer layer is modified by treatment with sodium hypochlorite.

9. (Previously Presented)     The method of claim 1, wherein the spacer layer comprises a chromophore.

10. (Previously Presented)     The method of claim 1, wherein the layer formed of metallic clusters is deposited by sputtering or vapor deposition.

11. (Cancelled)

12. (Previously Presented) The method of claim 1, wherein said modifying the spacer layer is performed by a PVD process.

13. (Previously Presented) The method of claim 1, wherein said modifying the spacer layer is performed by a CVD process.

14. (Previously Presented) The method of claim 1, wherein said modifying the spacer layer is performed by treatment with oxidizing fluids.

15. (Cancelled)

16. (Previously Presented) The method of claim 2, wherein said modifying the spacer layer is performed by a PVD process.

17. (Previously Presented) The method of claim 2, wherein said modifying the spacer layer is performed by a CVD process.

18. (Previously Presented) The method of claim 2, wherein said modifying the spacer layer is performed by treatment with oxidizing fluids.

19. (Cancelled)